

**RM2308** 

#### N-Channel Enhancement Mode Power MOSFET

#### **Schematic Diagram**

## Description

The RM2308 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other switching application.

#### **General Features**

V<sub>DS</sub> =60V,I<sub>D</sub> =3A

 $R_{DS(ON)}$  <105m $\Omega$  @  $V_{GS}$ =10V

 $R_{DS(ON)}$  < 125m $\Omega$  @  $V_{GS}$ =4.5V

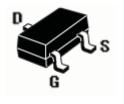
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

# 2308 G 1 2s

**Marking and Pin Assignment** 

#### **Application**

- Battery switch
- DC/DC converter
- Halogen-free



SOT-23 -3L Top View

#### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2308	RM2308	SOT-23-3L	Ø180mm	8 mm	3000 units

#### Absolute Maximum Ratings (T<sub>A</sub>=25℃unless otherwise noted)

<b>3</b> ( ):	,		
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	60	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	3	Α
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	10	А
Maximum Power Dissipation	P <sub>D</sub>	1.7	W
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	°C

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	R <sub>θJA</sub>	73.5	°C/W

#### **Electrical Characteristics (T<sub>A</sub>=25** ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	60	65	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V	-	-	1	μA

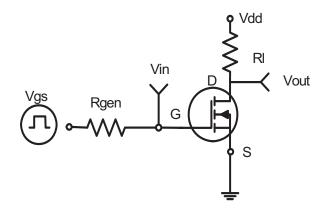
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=250\mu A$	1.0	1.2	1.9	V	
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =10V, $I_D$ =3A	-	78	105	mΩ	
Drain-Source On-State Resistance		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A	-	95	125	mΩ	
Forward Transconductance	<b>G</b> FS	V <sub>DS</sub> =15V,I <sub>D</sub> =2A	3	-	-	S	
Dynamic Characteristics (Note4)	·						
Input Capacitance	C <sub>lss</sub>	\/ -20\/\/ -0\/	-	247	-	PF	
Output Capacitance	Coss	$V_{DS}$ =30V, $V_{GS}$ =0V, F=1.0MHz	-	34	-	PF	
Reverse Transfer Capacitance	C <sub>rss</sub>	r-1.0ivinz	-	19.5	-	PF	
Switching Characteristics (Note 4)	·						
Turn-on Delay Time	t <sub>d(on)</sub>		-	6	-	nS	
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =30 $V$ , $I_{D}$ =1.5 $A$	-	15	-	nS	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10 $V$ , $R_{GEN}$ =1 $\Omega$	-	15	-	nS	
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS	
Total Gate Charge	$Q_g$	\/ -20\/   -2 1	-	6	-	nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =30V, $I_{D}$ =3A, $V_{GS}$ =4.5V	-	1	-	nC	
Gate-Drain Charge	$Q_{gd}$	V GS-4.3 V	-	1.3	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =3A	-	-	1.2	V	
Diode Forward Current (Note 2)	Is		-	-	3	Α	

#### **Notes:**

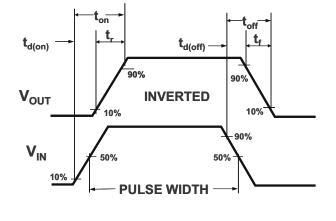
- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 Board, t ≤ 10 sec.
   Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



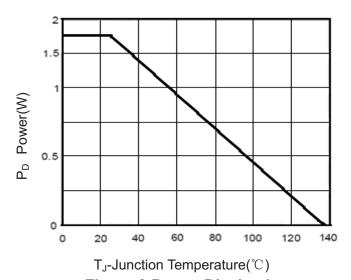
# **RATING AND CHARACTERISTICS CURVES (RM2308)**



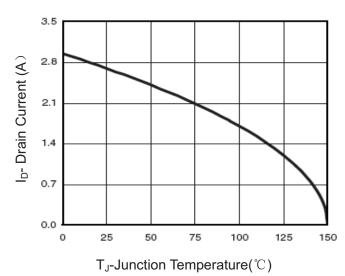
**Figure 1:Switching Test Circuit** 



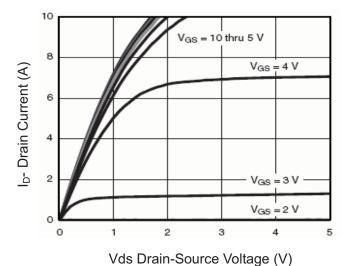
**Figure 2:Switching Waveforms** 



**Figure 3 Power Dissipation** 



**Figure 4 Drain Current** 



**Figure 5 Output Characteristics** 

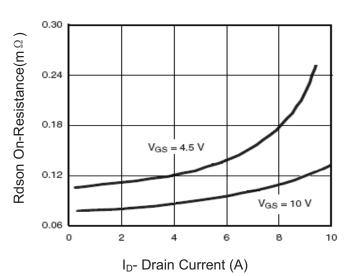
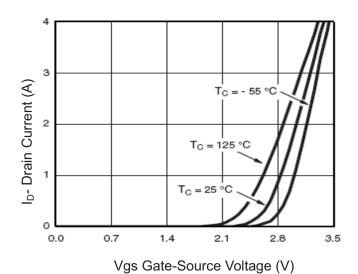


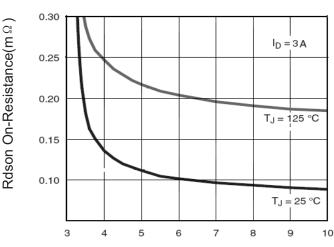
Figure 6 Drain-Source On-Resistance



# RATING AND CHARACTERISTICS CURVES (RM2308)



**Figure 7 Transfer Characteristics** 



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

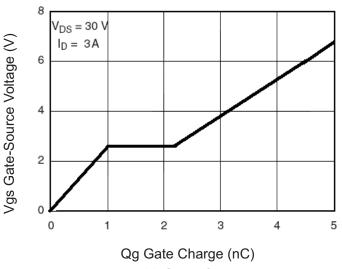


Figure 11 Gate Charge

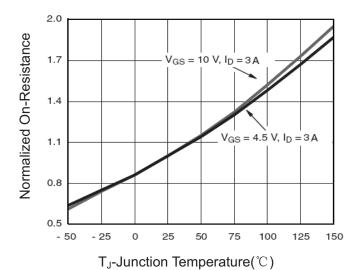
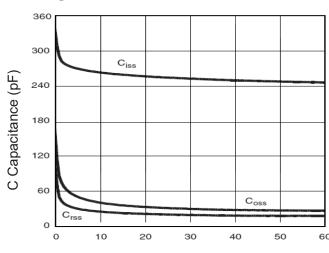


Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds

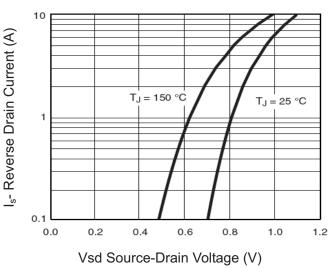


Figure 12 Source- Drain Diode Forward



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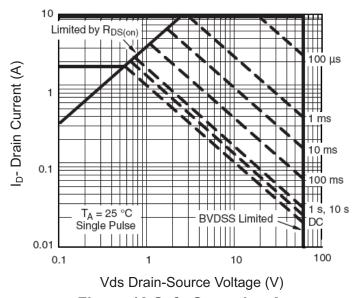


Figure 13 Safe Operation Area

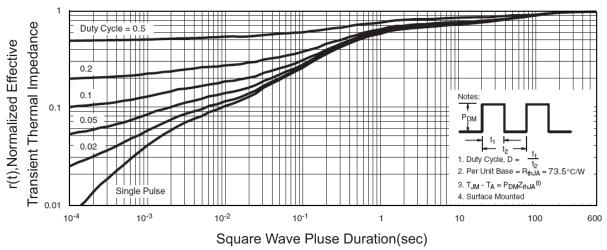
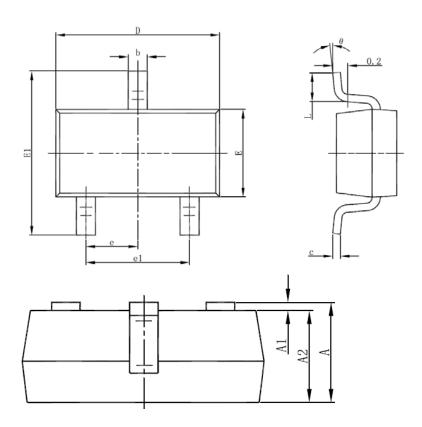


Figure 14 Normalized Maximum Transient Thermal Impedance



# **SOT-23-3L Package Information**



Combal	Dimensions Ir	n Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950(BSC)		0.037(	BSC)	
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

#### **Notes**

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- $5. \ Controlling \ dimension \ is \ millimeter, \ converted \ inch \ dimensions \ are \ not \ necessarily \ exact.$



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